ALPHANUMERIC INDEX — CROSS-REFERENCE (Continued)

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2N6411		MJE210	3-866
2N6412		MJE180	3-862
2N6413		MJE181	3-862
2N6414		MJE170	3-862
2N6415		MJE171	3-862
2N6416		MJE243	3-870
2N6417		MJE243	3-870
2N6418		MJE253	3-870
2N6419		MJE253	3-870
2N6420	2N6420		3-20
2N6421	2N6421		3-20
2N6422	2N6422		3-20
2N6423		2N6212	3-161
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2N6436	2N6436		3-203
2N6437	2N6437		3-203
2N6437JAN	2N6437JAN		3-203
2N6437JTX	2N6437JTX		3-203
2N6437JTXV	2N6437JTXV		3-203
2N6438	2N6438		3-203
2N6438JAN	2N6438JAN		3-203
2N6438JTX	2N6438JTX		3-203
2N6438JTXV	2N6438JTXV		3-203
2N6465		MJE15030	3-972
2N6466		MJE15030	3-972
2N6467		MJE15031	3-972
2N6468		MJE15031	3-972
2N6469		2N5879	3-123
2N6470		2N5881	3-123
2N6471		2N5881	3-123
2N6472		2N5882	3-123
2N6473		MJE15028	3-972
2N6474		MJE15028	3-972
2N6475		MJE15029	3-972
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2N6489	2N6489		3-207
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Industry Part Number	Motorola Direct Replacement	Motorola Similar Replacement	Page Number
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2N6535		TIP102	3-1091
2N6536		TIP102	3-1091
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2N6543	2N6543		3-215
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2N6546JTX	2N6546JTX		3-225
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2N6547JAN	2N6547JAN		3-225
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2N6609	2N6609		3-52
2N6648	2N6648		3-195
2N6648JAN	2N6648JAN		3-195
2N6648JTX	2N6648JTX		3-195
2N6648JTXV	2N6648JTXV		3-195
2N6649		2N6054	3-147
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2N6649JTX	2N6649JTX		—
2N6649JTXV	2N6649JTXV		—
2N6650JAN	2N6650JAN		—
2N6650JTX	2N6650JTX		—
2N6650JTXV	2N6650JTXV		—
2N6666		2N6667	3-232
2N6667	2N6667		3-232
2N6668	2N6668		3-232
2N6671JAN	2N6671JAN		—
2N6671JTX	2N6671JTX		—
2N6671JTXV	2N6671JTXV		—
2N6673JAN	2N6673JAN		—
2N6673JTX	2N6673JTX		—
2N6673JTXV	2N6673JTXV		—
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2N6677		MJ16010	3-758
2N6678		MJ16010	3-758
2N6833	2N6833		3-236
2N6834	2N6834		3-236
2N6835	MJ16006		3-742

*Consult Motorola if a direct replacement is necessary.

TABLE 1 — METAL TO-204, TO-204AE (continued)

I_{C}Cont Amps Max	$V_{CEO(sus)}$ Volts Min	Device Type NPN	Device Type PNP	h_{FE} Min/Max	@ I_C Amp	Resistive Switching t_s μs Max	Resistive Switching t_f μs Max	Resistive Switching @ I_C Amp	f_T MHz Min	P_D (Case) Watts @ 25°C
25	60	2N5885	2N5883	20/100	10	1	0.8	10	4	200
	80	2N5886	2N5884 2N6436	20/100 30/120	10 10	1 1	0.8 0.25	10 10	4 40	200 200
	100	2N6338	2N6437	30/120	10	1	0.25	10	40	200
	120	2N6339	2N6438	30/120	10	1	0.25	10	40	200
	125	BUV10 BUV10N		10 min 10 min	20 20	1.2 1.55	0.25 0.45	20 15	8 10	150 175
	140	2N6340		30/120	10	1	0.25	10	40	200
	150	2N6341		30/120	10	1	0.25	10	40	200
	500	BUT14##		15 min	16	2.8	0.8	16		175
28	400	BUT13##		20 min	20	2.6	0.8	18		175
30	40	2N3771 2N5301	 2N4398	15/60 15/60	15 15	 2	 1	 10	2 2	150 200
	60	2N5302 MJ11012##	2N4399 MJ11011##	15/60 1k min	15 20	2	1	10	2 4#	200 200
	90	BUX39 MJ11014##	 MJ11013##	8 min 1k min	20 20	1	0.25	20	8 4#	120 200
	100	2N6328 MJ802	 MJ4502	6/30 25/100	30 7.5				3 2	200 200
	120	MJ11016##	MJ11015##	1k min	20				4#	200
	325	BUV23•		8 min	16	1.8	0.4	16	8	250
	400	BUS98• BUX98		8 min	20	2.3 3	0.4 0.8	20 20		250 250
	450	BUS98A• BUX98A MJ16020• MJ16022•		8 min 5 min 7 min	16 30 30	2.3 3 1.8 1.5	0.4 0.8 0.2 0.15	16 16 20 20		250 250 250 250
40	160	BUV21N•		10 min	40	1	0.2	40	8	250
	200	BUV21•		10 min	25	1.8	0.4	25	8	150
	250	BUS52• BUV22•		15 min 10 min	40 20	 1.1	 0.35	 20	 8	350 250
	350	MJ10022•##		50/600	120	2.5	0.9	20		250
	400	MJ10023•##		50/600	10	2.5	0.9	20		250
	700	BUT35•##		15 min	24	4	1.2	24		250
50	60	2N5685• MJ11028•##	2N5683• MJ11029•##	15/60 400 min	25 50	0.5 typ	0.3 typ	25	2	300 300
	80	2N5686•	2N5684• 2N6377•	15/60 30/120	25 20	0.5 typ 0.8	0.3 typ 0.25	25 20	2 30	300 250
	90	MJ11030•##	MJ11031•##	400 min	50					300
	100	2N6274•	2N6378•	30/120	20	0.8	0.25	20	30	250
	120	2N6275• MJ11032•##	2N6379• MJ11033•##	30/120 400 min	20 50	0.8	0.25	20	30	250 300
	125	BUV20•		10 min	50	1.2	0.25	50	8	250
	150	2N6277•		30/120	20	0.8	0.25	20	30	250

• Modified TO-3 60 mil pins, # $|h_{fe}|$ @ 1 MHz, ## Darlington

(continued)

☐ JAN, JTX, JTXV Available

TABLE 13 — POWER SWITCHING TRANSISTORS (continued)

I_C Cont Amps Max	$V_{CEO(sus)}$ Volts Min	Device Type NPN	Device Type PNP	h_{FE} Min/Max	@ I_C Amp	Resistive Switching t_s μs Max	Resistive Switching t_f μs Max	Resistive Switching @ I_C Amp	f_T MHz Min	P_D (Case) Watts @ 25°C	Case JEDEC/MOT
4	30	BD185		15 min	2				20	40	TO-225AA/77
	45	BD785	BD786	20 min	2				50	15	TO-225AA/77
	60	2N4877		20/100	4	1.5	0.5	4	30	10	TO-205AD/79
		BD189		15 min	2				20	40	TO-225AA/77
		BD787	BD788	20 min	2				50	15	TO-225AA/77
	80	BD789	BD790	10 min	2				40	15	TO-225AA/77
	100	BD791	BD792	10 min	2				40	15	TO-225AA/77
5	80	2N5337	2N6191	60/240	2	2	0.2	2	30	10	TO-205AD/79
	100	2N5339	2N6193	60/240	2	2	0.2	2	30	10	TO-205AD/79
7	60	2N6315	2N6317	20/100	2.5	1	0.8	2.5	4	90	TO-213AA/80
	80	2N5428		60/240	2	2	0.2	2	30	60	TO-213AA/80
		2N6316	2N6318	20/100	2.5	1	0.8	2.5	4	90	TO-213AA/80
	100	2N5430		60/240	2	2	0.2	2	30	60	TO-213AA/80
7.5	60	2N3447		40/120	5	2	0.35	5	10	115	TO-204/1
	80	2N3448		40/120	5	2	0.35	5	10	115	TO-204/1
8	120	MJE15028	MJE15029	20 min	4	0.4 typ	0.18 typ	5	30	50	TO-220/221A
	150	MJE15030	MJE15031	20 min	4	0.4 typ	0.18 typ	5	30	50	TO-220/221A
10	60	2N5877	2N5875	20/100	4	1	0.8	4	4	150	TO-204/1
	80	2N5878	2N5876	20/100	4	1	0.8	4	4	150	TO-204/1
15	60	2N5881	2N5879	20/100	6	1	0.8	6	4	160	TO-204/1
	80	2N5882	2N5880	20/100	6	1	0.8	6	4	160	TO-204/1
18	160	BUX41N		8 min	12	1.2	0.25	12	8	120	TO-204/1
20	75	2N5039		20/100	10	1.5	0.5	10	60	140	TO-204/1
	80	2N5303	2N5745	15/60	10	2	1	10	2	200	TO-204/1
	90	2N5038		20/100	12	1.5	0.5	12	60	140	TO-204/1
	125	BUX40		8 min	15	1	0.25	15	8	120	TO-204/1
	160	BUV11N		10 min	15	1.2	0.25	15	8	150	TO-204/1
25	60	2N5885	2N5883	20/100	10	1	0.8	10	4	200	TO-204/1
	80	2N5886	2N5884	20/100	10	1	0.8	10	4	200	TO-204/1
			2N6436	30/120	10	1	0.25	10	40	200	TO-204/1
	100	2N6338	2N6437	30/120	10	1	0.25	10	40	200	TO-204/1
	120	2N6339	2N6438	30/120	10	1	0.25	10	40	200	TO-204/1
	125	BUV10		10 min	20	1.2	0.25	20	8	150	TO-204/1
		BUV10N		10 min	20	1.55	0.45	15	10	175	TO-204/1
	140	2N6340		30/120	10	1	0.25	10	40	200	TO-204/1
	150	2N6341		30/120	10	1	0.25	10	40	200	TO-204/1
30	40	2N5301	2N4398	15/60	15	2	1	10	2	200	TO-204/1
	60	2N5302	2N4399	15/60	15	2	1	10	2	200	TO-204/1
	90	BUX39		8 min	20	1	0.25	20	8	120	TO-204/1

(continued)

2N6420 thru 2N6422
See Page 3-20

2N6436
2N6437, 2N6438

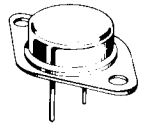
HIGH-POWER PNP SILICON TRANSISTORS

. . . designed for use in industrial-military power amplifier and switching circuit applications.

- High Collector-Emitter Sustaining Voltage –
  $V_{CEO(sus)}$ = 80 Vdc (Min) – 2N6436
  = 100 Vdc (Min) – 2N6437
  = 120 Vdc (Min) – 2N6438
- High DC Current Gain –
  h_{FE} = 20-80 @ I_C = 10 Adc
  = 12 (Min) @ I_C = 25 Adc
- Low Collector-Emitter Saturation Voltage –
  $V_{CE(sat)}$ = 1.0 Vdc (Max) @ I_C = 10 Adc
- Fast Switching Times @ I_C = 10 Adc
  t_r = 0.3 μs (Max)
  t_s = 1.0 μs (Max)
  t_f = 0.25 μs (Max)
- Complement to NPN 2N6338 thru 2N6341

25 AMPERE
POWER TRANSISTORS
PNP SILICON

80, 100, 120 VOLTS
200 WATTS



*MAXIMUM RATINGS

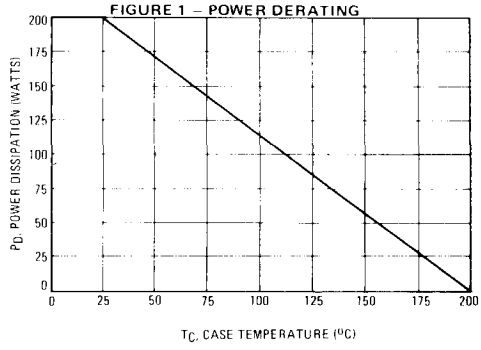
Rating	Symbol	2N6436	2N6437	2N6438	Unit
Collector-Base Voltage	V_{CB}	100	120	140	Vdc
Collector-Emitter Voltage	V_{CEO}	80	100	120	Vdc
Emitter-Base Voltage	V_{EB}	6.0			Vdc
Collector Current — Continuous Peak	I_C	25 50			Adc
Base Current	I_B	10			Adc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	200 1.14			Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200			°C

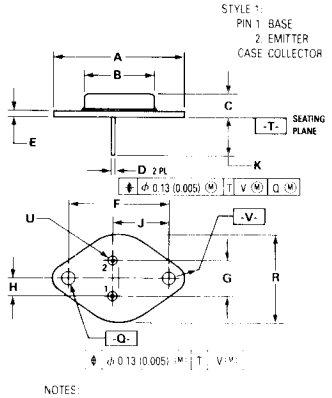
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.875	°C/W

*Indicates JEDEC Registered Data.

FIGURE 1 – POWER DERATING





NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	—	39.37	—	1.550
B	—	21.08	—	0.830
C	6.35	8.25	0.250	0.325
D	0.97	1.09	0.038	0.043
E	1.40	1.77	0.055	0.070
F	30.15 BSC		1.187 BSC	
G	10.92 BSC		0.430 BSC	
H	5.46 BSC		0.215 BSC	
J	16.89 BSC		0.665 BSC	
K	11.18	12.19	0.440	0.480
Q	3.84	4.19	0.151	0.165
R		26.67	—	1.050
U	4.83	5.33	0.190	0.210
V	3.84	4.19	0.151	0.165

CASE 1-06
TO-204AA
(TO-3)

3

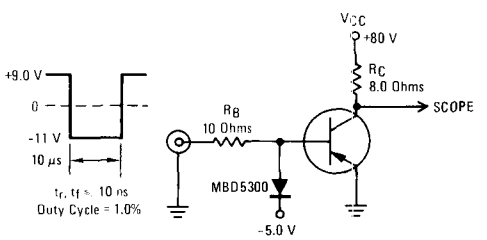
***ELECTRICAL CHARACTERISTICS** (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage (1)		$V_{CEO(sus)}$			Vdc
(I_C = 50 mAdc, I_B = 0)	2N6436		80	–	
	2N6437		100	–	
	2N6438		120	–	
Collector Cutoff Current		I_{CEO}			μAdc
(V_{CE} = 40 Vdc, I_B = 0)	2N6436		–	50	
(V_{CE} = 50 Vdc, I_B = 0)	2N6437		–	50	
(V_{CE} = 60 Vdc, I_B = 0)	2N6438		–	50	
Collector Cutoff Current		I_{CEX}			μAdc
(V_{CE} = 90 Vdc, $V_{BE(off)}$ = -1.5 Vdc)	2N6436		–	10	
(V_{CE} = 110 Vdc, $V_{BE(off)}$ = -1.5 Vdc)	2N6437		–	10	
(V_{CE} = 130 Vdc, $V_{BE(off)}$ = -1.5 Vdc)	2N6438		–	10	
(V_{CE} = 80 Vdc, $V_{BE(off)}$ = -1.5 Vdc, T_C = 150°C)	2N6436		–	1.0	mAdc
(V_{CE} = 100 Vdc, $V_{BE(off)}$ = -1.5 Vdc, T_C = 150°C)	2N6437		–	1.0	
(V_{CE} = 120 Vdc, $V_{BE(off)}$ = -1.5 Vdc, T_C = 150°C)	2N6438		–	1.0	
Collector Cutoff Current		I_{CBO}			μAdc
(V_{CB} = 100 Vdc, I_E = 0)	2N6436		–	10	
(V_{CB} = 120 Vdc, I_E = 0)	2N6437		–	10	
(V_{CB} = 140 Vdc, I_E = 0)	2N6438		–	10	
Emitter Cutoff Current (V_{EB} = 6.0 Vdc, I_C = 0)		I_{EBO}	–	100	μAdc
ON CHARACTERISTICS					
DC Current Gain (1)		h_{FE}			–
(I_C = 0.5 Adc, V_{CE} = 2.0 Vdc)			30		
(I_C = 10 Adc, V_{CE} = 2.0 Vdc)			20	120	
(I_C = 25 Adc, V_{CE} = 2.0 Vdc)			12		
Collector-Emitter Saturation Voltage (1)		$V_{CE(sat)}$			Vdc
(I_C = 10 Adc, I_B = 1.0 Adc)			–	1.0	
(I_C = 25 Adc, I_B = 2.5 Adc)			–	1.8	
Base-Emitter Saturation Voltage (1)		$V_{BE(sat)}$			Vdc
(I_C = 10 Adc, I_B = 1.0 Adc)			–	1.8	
(I_C = 25 Adc, I_B = 2.5 Adc)				2.5	
DYNAMIC CHARACTERISTICS					
Current-Gain – Bandwidth Product (I_C = 1.0 Adc, V_{CE} = 10 Vdc, f_{test} = 10 MHz)		f_T	40	–	MHz
Output Capacitance (V_{CE} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{ob}	–	700	pF
SWITCHING CHARACTERISTICS					
Rise Time (V_{CC} = 80 Vdc, I_C = 10 A, $V_{BE(off)}$ = 6.0 Vdc, I_{B1} = 1.0 Adc)		t_r	–	0.3	μs
Storage (V_{CC} = 80 Vdc, I_C = 10 A, $V_{BE(off)}$ = 6.0 Vdc, I_{B1} = I_{B2} = 1.0 Adc)		t_s	–	1.0	μs
Fall Time (V_{CC} = 80 Vdc, I_C = 10 A, $V_{BE(off)}$ = 6.0 Vdc, I_{B1} = I_{B2} = 1.0 Adc)		t_f	–	0.25	μs

*Indicates JEDEC Registered Data.

(1) Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%.

FIGURE 2 – SWITCHING TIME TEST CIRCUIT



Note: For information on Figures 3 and 6, R_B and R_C were varied to obtain desired test conditions.

FIGURE 3 – TURN-ON TIME

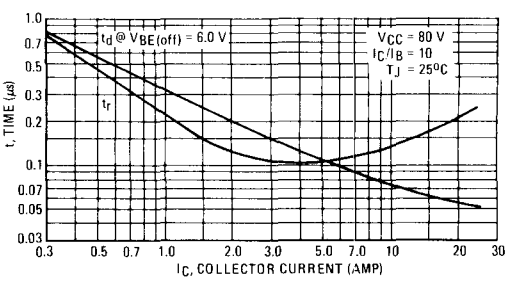


FIGURE 4 – THERMAL RESPONSE

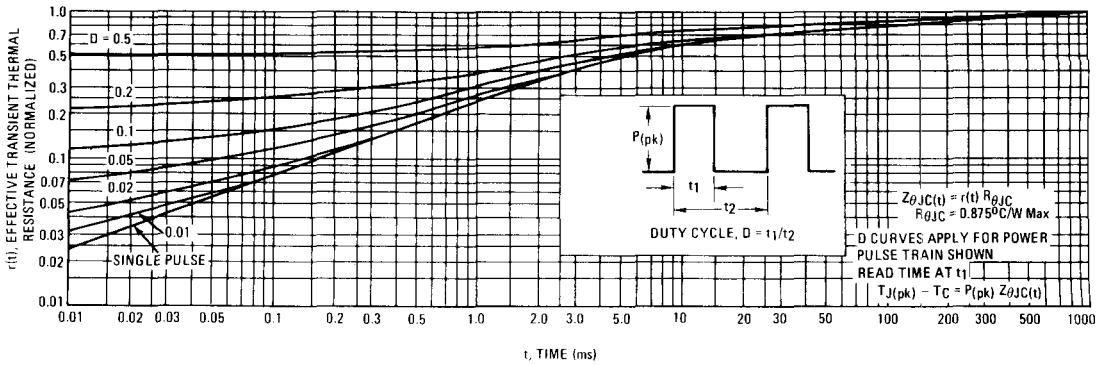
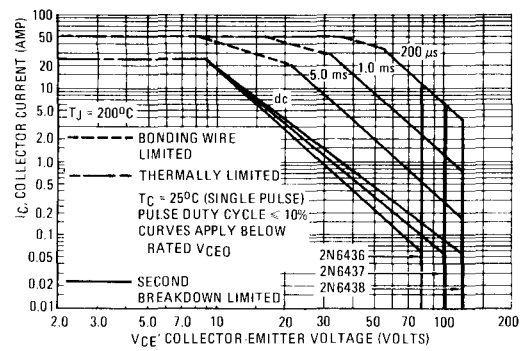


FIGURE 5 – ACTIVE REGION SAFE OPERATING AREA



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 200^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 200^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

FIGURE 6 – TURN-OFF TIME

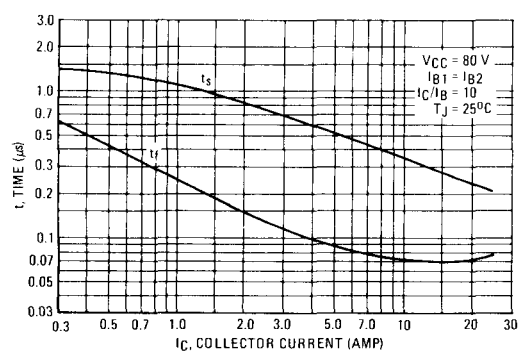
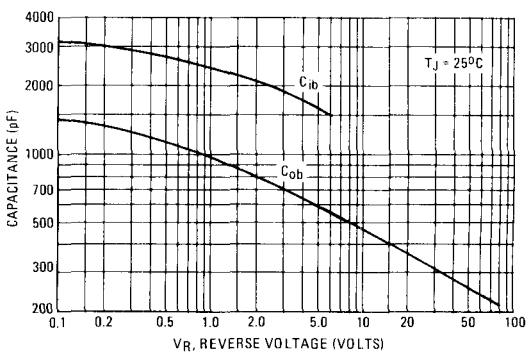


FIGURE 7 – CAPACITANCE



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